

UTC2SC945 NPNEPITAXIAL SILICON TRANSISTOR

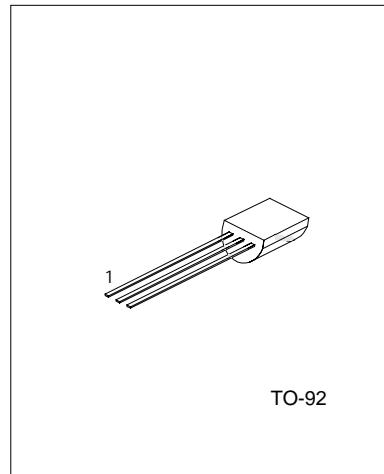
AUDIO FREQUENCY AMPLIFIER
HIGH FREQUENCY OSC NPN
TRANSISTOR

DESCRIPTION

The UTC 2SC945 is an audio frequency amplifier high frequency OSC NPN transistor.

FEATURES

- *Collector-Emitter voltage:
 $BV_{CEO}=50V$
- *Collector current up to 150mA
- *High hFE linearity
- *Complimentary to 2SA733



1:EMITTER 2:COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$, unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Dissipation($T_a=25^{\circ}C$)	P_c	250	mW
Collector Current	I_c	150	mA
Base Current	I_b	50	mA
Junction Temperature	T_j	125	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c=100\mu A, I_E=0$	60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c=10mA, I_B=0$	50			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=40V, I_E=0$			100	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=3V, I_C=0$			100	nA
DC Current Gain(note)	h_{FE}	$V_{CE}=6V, I_c=1mA$	90		600	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=100mA, I_B=10mA$		0.1	0.3	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_c=50mA$	100	190		MHz
Output Capacitance	C_{OB}	$V_{CB}=10V, I_E=0, f=1MHz$		2.0	3.0	pF
Noise Figure	NF	$I_c=-0.1mA, V_{CE}=6V$ $R_g=10k\Omega, f=100Hz$		4.0	6.0	dB

UTC2SC945 NPNEPITAXIAL SILICON TRANSISTOR

CLASSIFICATION OF hFE

RANK	R	Q	P	K
RANGE	90-180	135-270	200-400	300-600

TYPICAL PERFORMANCE CHARACTERISTICS

Fig.1 Static characteristics

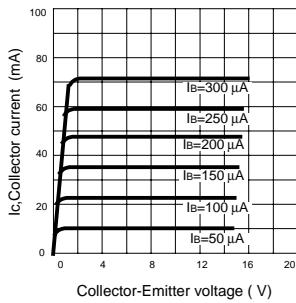


Fig.2 DC current Gain

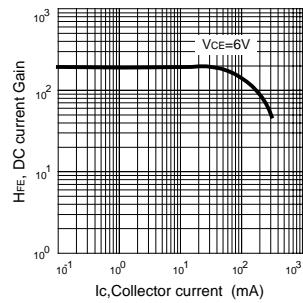


Fig.3 Base-Emitter on Voltage

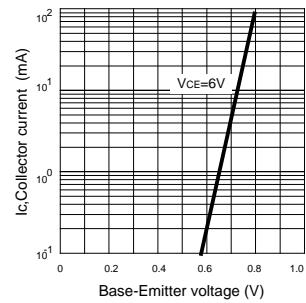


Fig.4 Saturation voltage

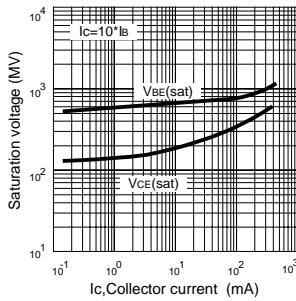


Fig.5 Current gain-bandwidth product

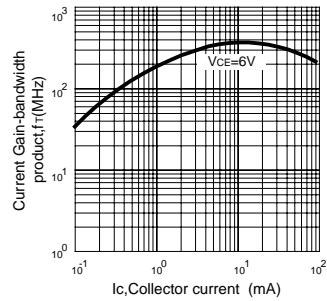


Fig.6 Collector output Capacitance

